Power Transistor (–60V, –3A)

2SB1184 / 2SB1243

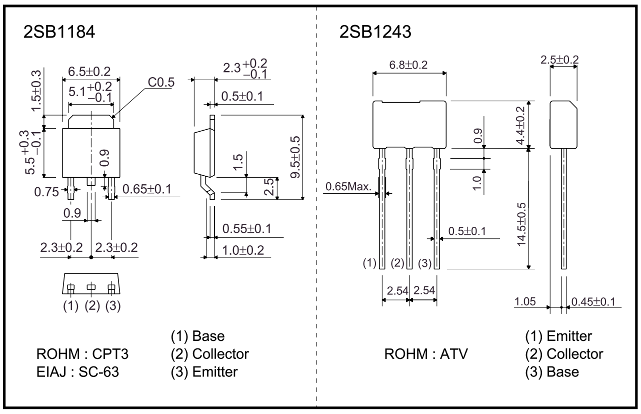
●Features

1) Low $V_{CE(sat)}$.
   $V_{CE(sat)}$ = -0.5V (Typ.)
   (I_C/I_B = -2A / -0.2A)
2) Complements the 2SD1760 / 2SD1864.

●Structure

Epitaxial planar type
PNP silicon transistor

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	–60	V
Collector-emitter voltage		V_{CEO}	–50	V
Emitter-base voltage		V_{EBO}	–5	V
Collector current		I_C	–3	A (DC)
		I_{CP}	–4.5	A (Pulse) ∗1
Collector power dissipation	2SB1184	P_C	1	W
			15	W (T_C=25°C)
	2SB1243		1	W ∗2
Junction temperature		Tj	150	°C
Storage temperature		Tstg	–55~+150	°C

∗1 Single pulse, Pw=100ms
∗2 Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.